

2SK2684(L), 2SK2684(S)

Silicon N Channel MOS FET High Speed Power Switching

REJ03G1022-0200

(Previous: ADE-208-542)

Rev.2.00

Sep 07, 2005

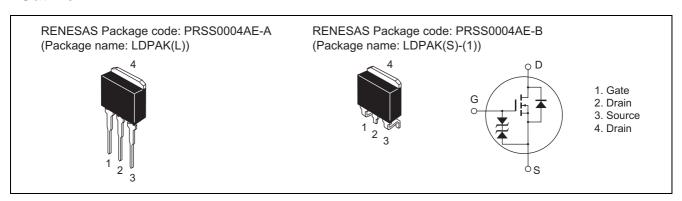
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- · Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	30	А
Drain peak current	I _{D(pulse)} *1	120	А
Body to drain diode reverse drain current	I _{DR}	30	А
Channel dissipation	Pch*2	50	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

2. Value at Tc = 25°C

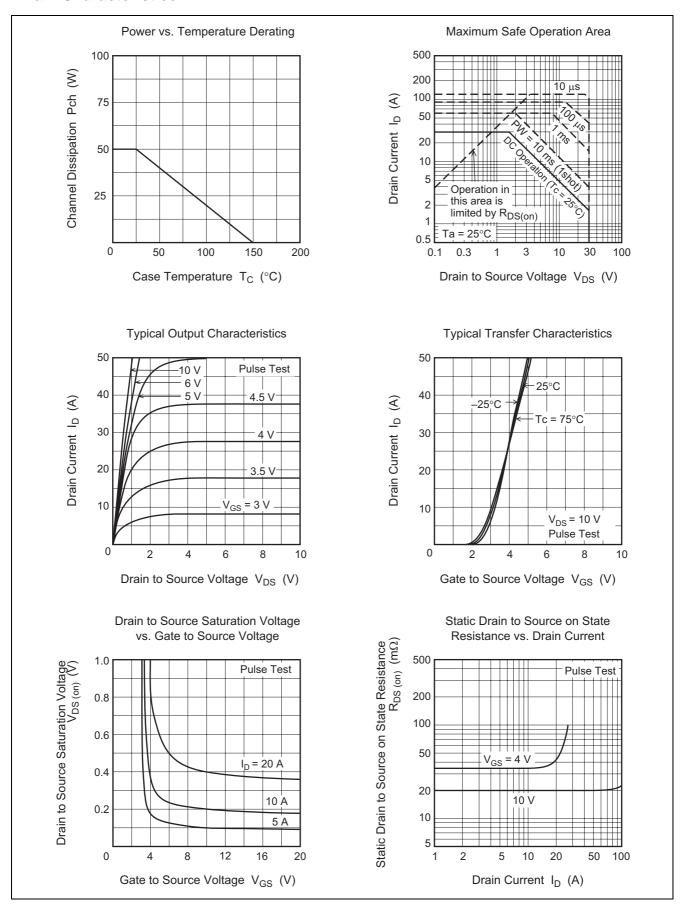
Electrical Characteristics

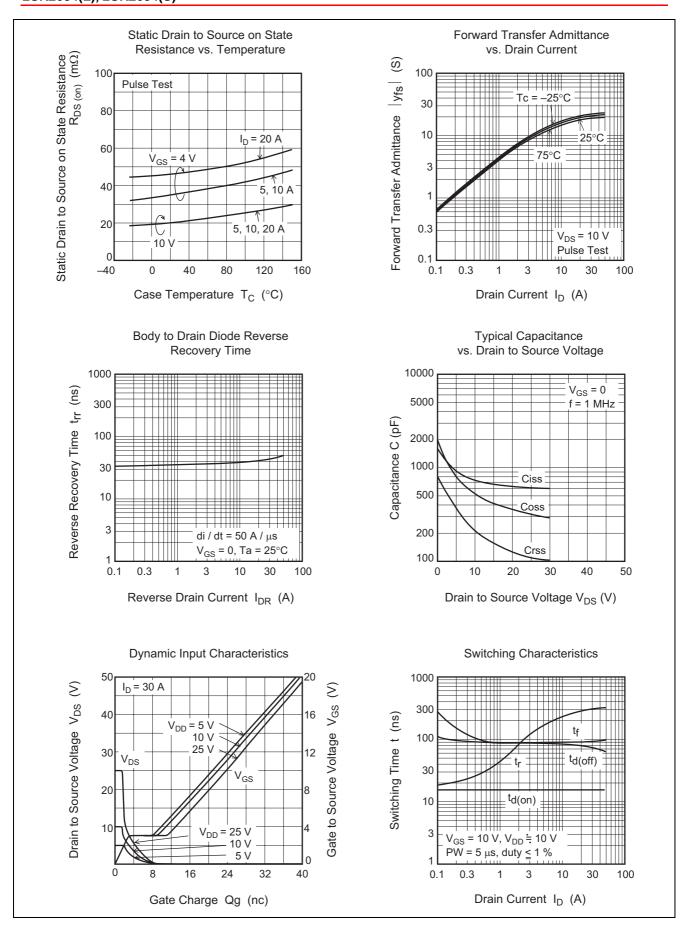
 $(Ta = 25^{\circ}C)$

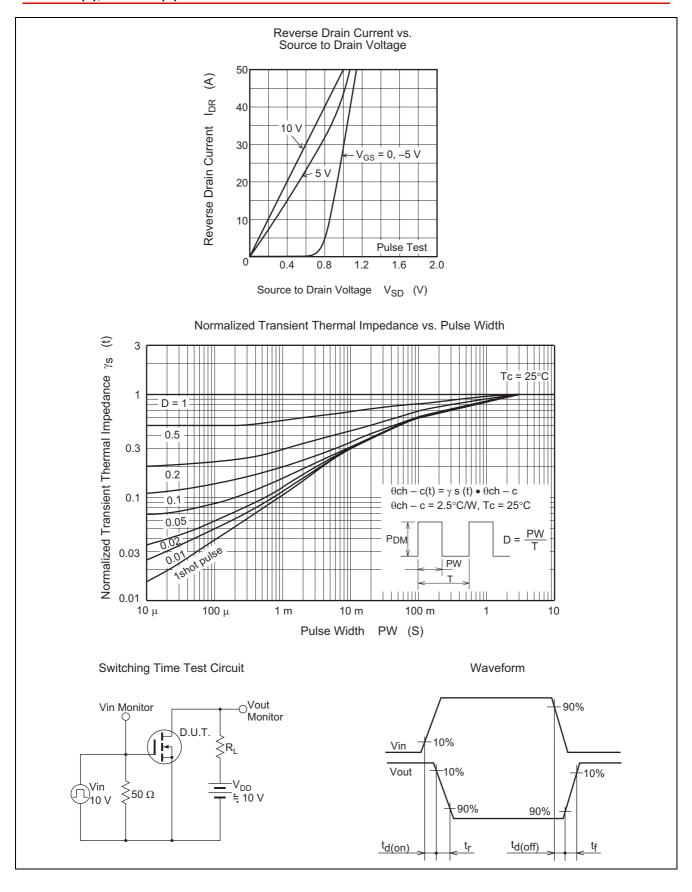
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	10	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source leak current	I_{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R _{DS(on)}	_	20	28	mΩ	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$
resistance	R _{DS(on)}	_	35	50	mΩ	$I_D = 15 \text{ A}, V_{GS} = 4 \text{ V}^{*3}$
Forward transfer admittance	y _{fs}	12	18	_	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$
Input capacitance	Ciss	_	750	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	520	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	210	_	pF]
Turn-on delay time	t _{d(on)}	_	16	_	ns	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A},$
Rise time	t _r	_	260	_	ns	$R_L = 0.67 \Omega$
Turn-off delay time	t _{d(off)}	_	85	_	ns]
Fall time	t _f	_	90	_	ns]
Body to drain diode forward voltage	V_{DF}	_	1.0	_	V	$I_F = 30 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery	t _{rr}	_	45	_	ns	I _F = 30 A, V _{GS} = 0
time						$di_F/dt = 50 A/\mu s$

Note: 3. Pulse test

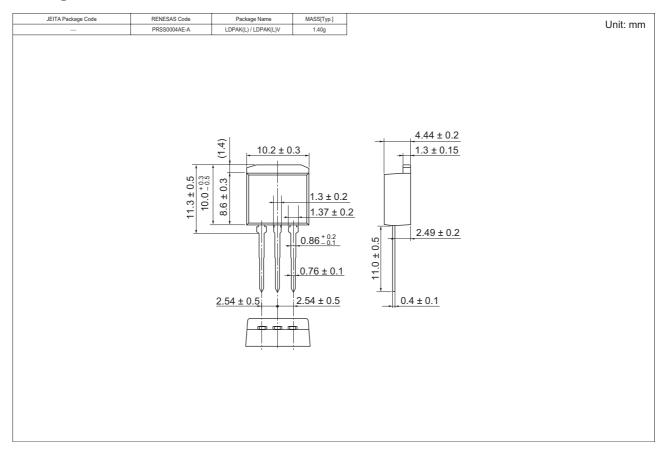
Main Characteristics

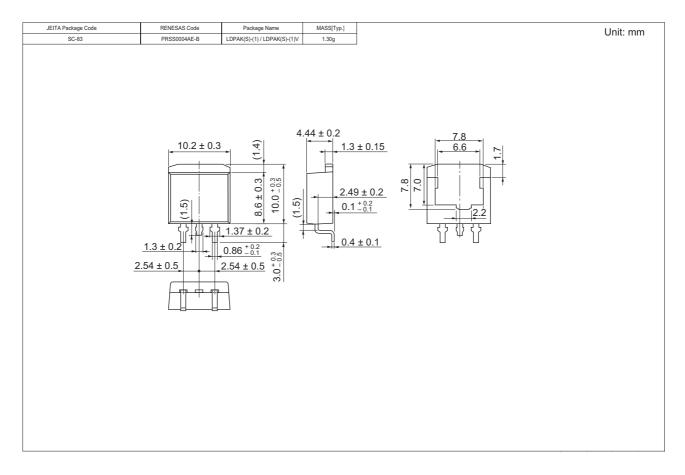






Package Dimensions





Ordering Information

Part Name	Quantity	Shipping Container
2SK2684L-E	500 pcs	Box (Sack)
2SK2684STL-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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